

Schottky barrier diode

RB160L-60

● Applications

High frequency rectification
For switching power supply.

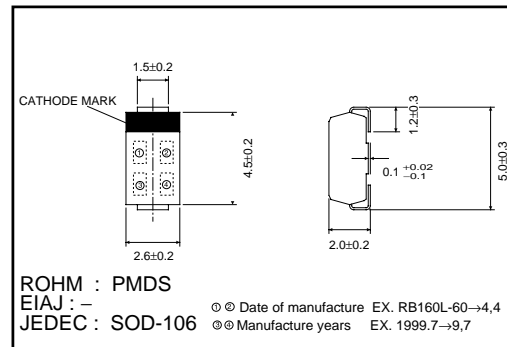
● Features

- 1) Compact power mold (PMDS)
- 2) Low V_F . ($V_F=0.55V$ Typ. at 1A)
- 3) High reliability

● Construction

Silicon epitaxial Planar

● External dimensions (Units : mm)



● Absolute maximum ratings ($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Limits	Unit
Peak reverse voltage	V_{RM}	60	V
DC reverse voltage	V_R	60	V
Mean rectifying current *	I_o	1	A
Peak forward surge current	I_{FSM}	30	A
Junction temperature	T_j	125	$^\circ\text{C}$
Storage temperature	T_{stg}	-40 ~ +125	$^\circ\text{C}$

* When mounted on a PCBs board

● Electrical characteristics ($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Forward voltage	V_F	-	-	0.58	V	$I_F = 1.0A$
Reverse current	I_R	-	-	0.5	mA	$V_R = 60V$

Diodes

● Electrical characteristic curves (Ta = 25°C)

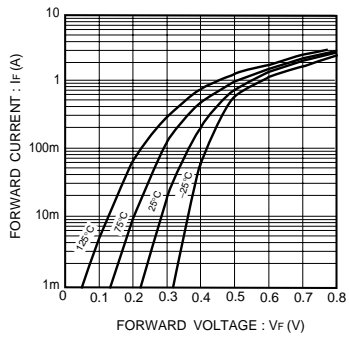


Fig.1 Forward characteristics

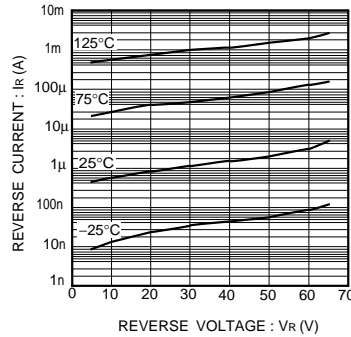


Fig.2 Reverse characteristics

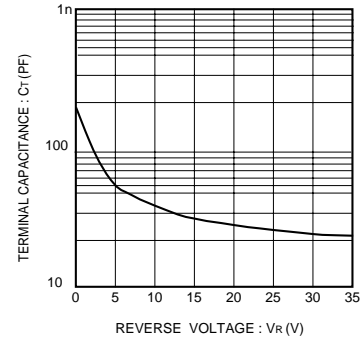


Fig.3 Capacitance between terminals characteristics

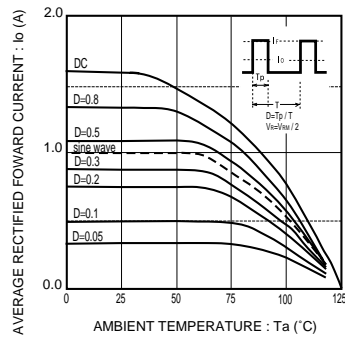


Fig.4 Derating curve (Io-Ta)

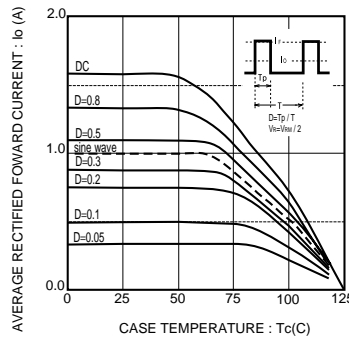


Fig.5 Derating curve (Io-Tc)